Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- Very fast switching
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection

3. Applications

- Relay driver
- · High-speed line driver
- Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor				'		
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	170	mA
Static chara	acteristics (per transistor)					'	
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 170 \text{ mA}; T_j = 25 ^{\circ}\text{C}$		-	3	4.5	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1	654	
3	D2	drain TR2		G1
4	S2	source TR2	0	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	TSSOP6 (SOT363)	S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
NX138AKS		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
NX138AKS	F8%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or					
V_{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	110	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	680	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	265	mW
			[1]	-	325	mW
		T _{sp} = 25 °C		-	1.33	W
Per device						
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode		'	'		
Is	source current	T _{amb} = 25 °C	[1]	-	170	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

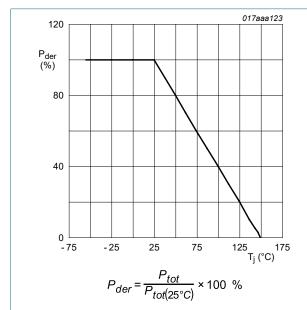


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

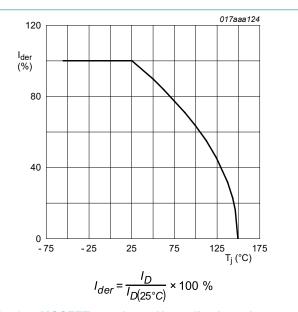


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

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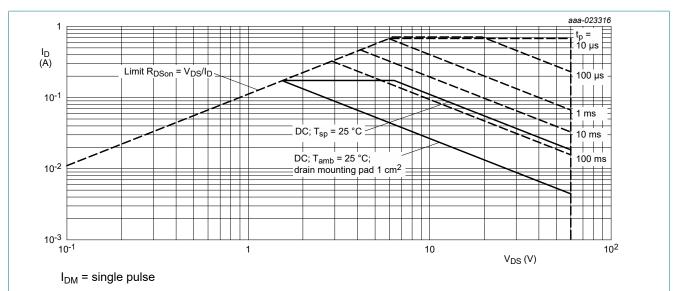


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

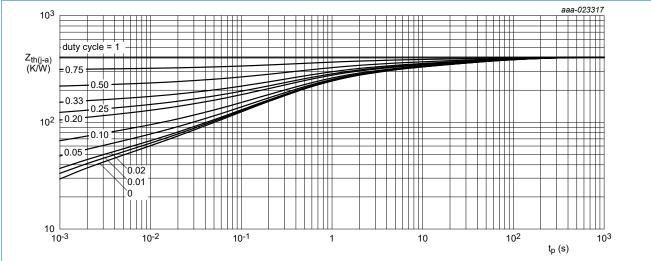
60 V, dual N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	500	560	K/W
junction to ambient		[2]	-	450	480	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	100	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

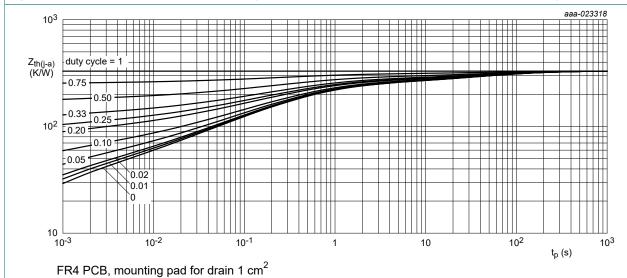


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.8	1.1	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.5	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 170 mA; T _j = 25 °C	-	3	4.5	Ω
		V _{GS} = 10 V; I _D = 170 mA; T _j = 150 °C	-	6	9	Ω
		$V_{GS} = 5 \text{ V}; I_D = 150 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	3.7	5.2	Ω
		$V_{GS} = 4 \text{ V}; I_D = 130 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	4	6.3	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	5	10	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 170 mA; T_{j} = 25 °C	-	3.5	-	S
Dynamic ch	naracteristics (per transist	or)	'			
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 170 mA; V _{GS} = 10 V;	-	0.9	1.4	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	15	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.3	-	pF
C _{rss}	reverse transfer capacitance		-	1.5	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 170 mA; V _{GS} = 10 V;	-	8	12	ns
t _r	rise time	$R_{G(ext)} = 75 \Omega; T_j = 25 °C$	-	10	-	ns
t _{d(off)}	turn-off delay time		-	8	20	ns
t _f	fall time	7	-	5	-	ns
Source-dra	in diode (per transistor)	-	1			
V _{SD}	source-drain voltage	I _S = 170 mA; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

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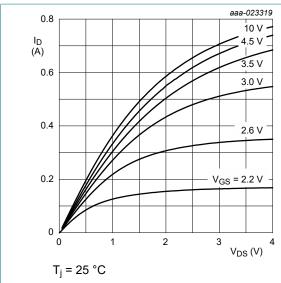
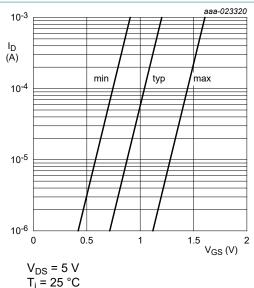


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}\text{C}$

Sub-threshold drain current as a function of Fig. 7. gate-source voltage

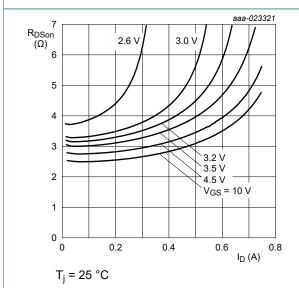


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

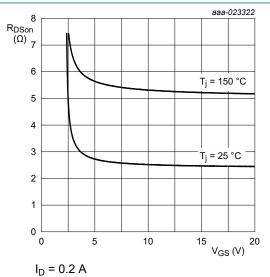


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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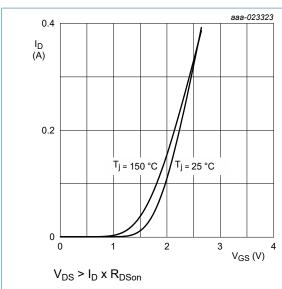


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

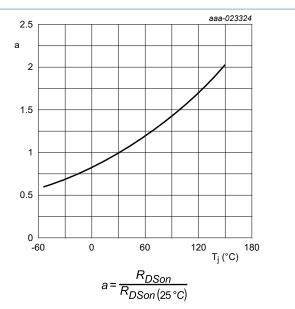


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

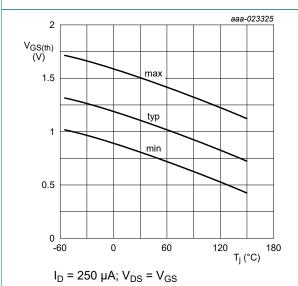


Fig. 12. Gate-source threshold voltage as a function of junction temperature

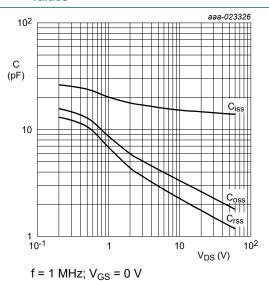


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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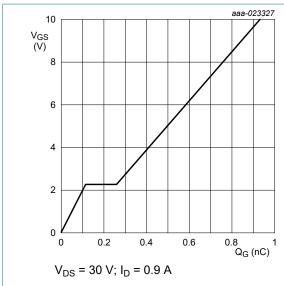


Fig. 14. Gate-source voltage as a function of gate charge; typical values

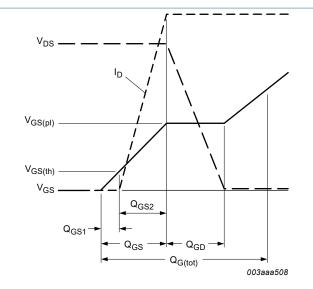


Fig. 15. Gate charge waveform definitions

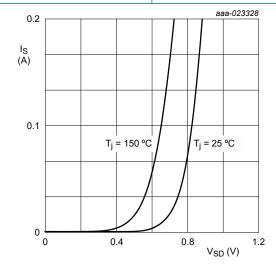
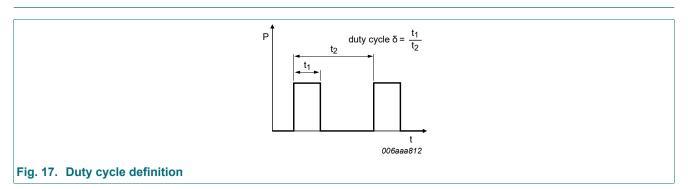


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

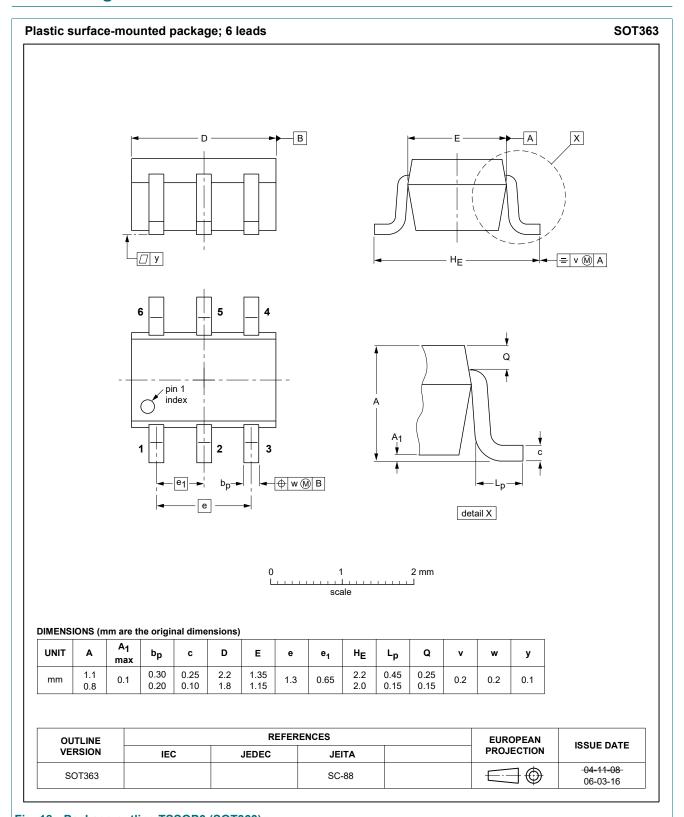
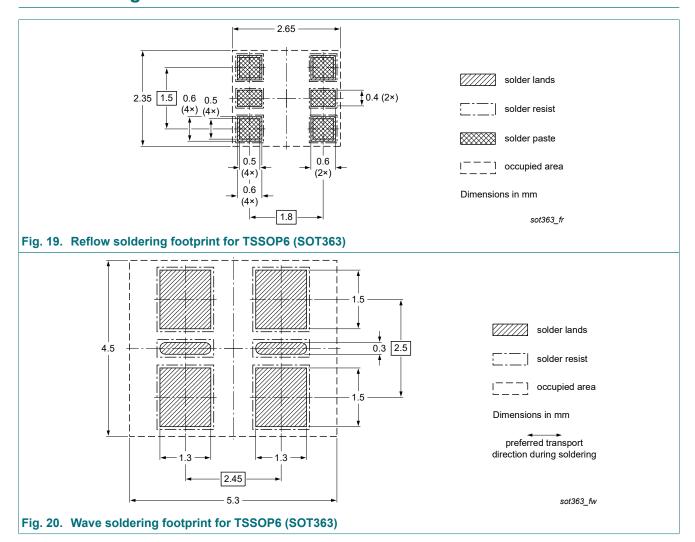


Fig. 18. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID Release date		Data sheet status	Change notice	Supersedes				
NX138AKS v.2	20240202	Product data sheet	-	NX138AKS v.1				
Modifications:	Chapter "Characteri	Chapter "Characteristics": typo correction for one R _{DSon} condition						
NX138AKS v.1	20160615	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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